

Room-temperature waveguide-integrated photodetector using bolometric effect for mid-infrared spectroscopy applications

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Abstract

Waveguide-integrated mid-infrared (MIR) photodetectors are pivotal components for developing molecular spectroscopy applications, leveraging mature photonic integrated circuit (PIC) technologies. Despite various strategies, critical challenges still remain in achieving broadband photoresponse, cooling-free operation, and large-scale complementary-metal-oxide-semiconductor (CMOS)-compatible manufacturability. To leap beyond these limitations, the bolometric effect – a thermal detection mechanism – is introduced into the waveguide platform. More importantly, we pursue a free-carrier absorption (FCA) process in germanium (Ge) to create an efficient light-absorbing medium, providing a pragmatic solution for full coverage of the MIR spectrum without incorporating exotic materials into CMOS. Here, we present an uncooled waveguide-integrated photodetector based on a Ge-on-insulator (Ge-OI) PIC architecture, exploiting the bolometric effect combined with FCA. Notably, our device exhibits a broadband responsivity of ~ 12 mA/W across 4030–4360 nm (and potentially beyond), challenging the state of the art, while achieving a noise-equivalent power of 3.4×10^{-9} W/Hz^{0.5} at 4180 nm. We further demonstrate label-free sensing of carbon dioxide using our integrated photodetector and sensing waveguide on a single chip. This approach to room-temperature waveguide-integrated MIR photodetection, harnessing bolometry with FCA in Ge, not only facilitates the realization of fully integrated lab-on-a-chip systems with wavelength flexibility but also provides a blueprint for MIR PICs with CMOS-foundry-compatibility.

Introduction

The mid-infrared (MIR) spectral region beyond 3 μm is of enormous scientific and technological importance, as it encompasses unique molecular fingerprints¹⁻³, enabling sophisticated chemical and biological analysis in a non-invasive manner through absorption spectroscopy techniques^{4,5}. Leveraging highly mature photonic integrated circuit (PIC) technologies⁶⁻⁸, substantial progress has been made in miniaturizing traditional external-optics-based spectrometers into chip-scale systems that offer cost-effective, mass-manufacturable, and scalable solutions⁹⁻¹². A key bottleneck in realizing fully integrated and robust lab-on-a-chip systems is the monolithic integration of MIR photodetectors (PDs) into the waveguide platforms. Traditionally, surface-illuminated MIR PDs have relied on narrow-bandgap semiconductor materials such as HgCdTe alloy¹³ and III-V compounds¹⁴; yet, they necessitate cryogenic cooling (bulky and costly) to mitigate high thermal noise at room temperature, posing severe challenges in practical applications¹⁵. More recently, two-dimensional materials (e.g., graphene¹⁶ and black phosphorus¹⁷) have arisen as promising candidates that can be operated at room temperature¹⁸. However, the zero-bandgap nature of graphene results in an extremely high dark current level under biasing¹⁹. Additionally, black phosphorus itself exhibits severe performance degradation under ambient conditions and possesses an absorption edge of around 4 μm ²⁰, restricting its utility to longer wavelengths. These emerging materials also still struggle with complementary-metal-oxide-semiconductor (CMOS)-compatible processes and wafer-scale integration, impeding large-scale and cost-saving production at commercialization levels²¹.

In this regard, it is highly beneficial for MIR photodetection to harness thermal-type PDs, where the photoresponse is extracted by converting photo-induced heat generation into the electrical signal^{18,22,23}, enabling wavelength-insensitive photodetection by tailoring the spectral characteristics of the absorber. Owing to the inherent nature of thermal detection, there is a slight compromise in response speed; however, a relatively moderate (or even low) level of bandwidth is adequate to meet the requirements for many MIR spectroscopy applications. To reap the full benefits of superior properties of the thermal detectors including wavelength independence and uncooled photodetection, here, we introduce the bolometric effect into the waveguide platform. Bolometers, a class of thermal-type PD, convert light-induced temperature fluctuations into changes in electrical resistance²³⁻²⁵. Notably, to date, few efforts have been devoted to achieving waveguide-integrated MIR photodetection beyond 3 μm using thermal detection mechanisms²⁶⁻²⁸. Optical absorbers with gold (Au) antennas on a suspended-Si waveguide have shown promise in bolometry in the range of 3.72–3.88 μm ^{26,27}; however, they offer low responsivities, and the resonance nature of the plasmonic structure intrinsically limits broadband photodetection. Additionally, the usage of noble metals is commonly restricted in CMOS foundries. A graphene-based detector on a chalcogenide glass (ChG)-on-CaF₂ waveguide using the photothermoelectric (PTE) effect, another class of thermal detection mechanism, operating at 5.2 μm , showed promising performances but is necessarily limited to a wavelength range of ~ 8 μm due to the

inherent material properties of the photonic platform²⁸. Furthermore, the use of exotic materials in CMOS processes and the complexity of fabrication pose significant challenges to practical implementation.

In this work, we remarkably advance the state of the art in waveguide-integrated MIR PDs by leveraging the bolometric effect with free-carrier absorption (FCA) in Ge^{29,30} and titanium oxide-based bolometric material^{31–33}, providing a pragmatic approach for uncooled MIR photodetection without foreign materials in CMOS or hybrid integrations. Our demonstration is based upon a CMOS-compatible Ge-on-insulator (Ge-OI) photonic platform with a buried oxide (BOX) of Y₂O₃ and a Si substrate, providing broad transparency window up to around 13 μm^{34,35}, and reaches record-high photoresponsivity for waveguide-integrated thermal-type PDs beyond 3 μm. Furthermore, to demonstrate the feasibility of non-destructive, label-free detection of molecules using our room-temperature-operated waveguide-integrated MIR PD, we have experimentally conducted carbon dioxide (CO₂) gas sensing by integrating the sensing waveguide and detector on a single chip.

Results

Device architecture and design. Figure 1a illustrates a schematic of the proposed MIR PIC-based sensor on the Ge-OI platform, comprising a slot waveguide for analyte sensing (passive sensing part) and a waveguide-integrated PD (detector part), monolithically integrated onto a single chip. Our on-chip photonic sensor utilizes light–analyte interaction within the sensing waveguide through absorption spectroscopy based on the Beer-Lambert law. An air-clad slot waveguide, supporting hollow-core guiding, has been employed to induce stronger light absorption with enhanced field confinement compared to conventional strip or rib waveguides, thus aiming to improve the sensitivity factor or to reduce the physical length of the sensing waveguide^{11,34}. The residual light is then directly coupled from the sensing waveguide into the waveguide-integrated PD. As noted earlier, the operational principle of our proposed detector is the bolometric effect combined with FCA in Ge. For the bolometric material that converts light-induced temperature variations into changes in electrical resistance, we employed a TiO₂/Ti/TiO₂ tri-layer film, whose temperature-dependent electrical properties can be finely tailored by engineering the thickness of each layer^{31–33}. The temperature change in bolometric detectors, in response to periodically varying incident light, can be described by²³

$$\Delta T = \frac{\eta \Phi_0}{\sqrt{G_{th}^2 + \omega^2 \cdot C_{th}^2}} \quad (1)$$

where ΔT represents the temperature change, η is the absorption efficiency for the given wavelength, ω and Φ_0 are the angular frequency and the amplitude of the periodic radiation, respectively, G_{th} is the thermal conductance between the detector and

the surrounding environment, and C_{th} is the thermal capacitance of the detector. As inferred from Equation (1), increasing η , while diminishing G_{th} and C_{th} , is critical for enhancing ΔT for a given incident optical power, which directly correlates with the bolometric detector's responsivity. In order to boost η within our PD, FCA in Ge should be elevated, which greatly depends on the type of free carriers and the doping concentration for particular wavelengths. To take full advantage of FCA in Ge, we selected a heavily-doped p -type Ge (p^+ Ge) as a MIR-absorbing medium (details can be found in [Supplementary Note 1](#)). For the reduction of G_{th} and C_{th} , the optimization of device geometries is crucial. Here, the optimization process, including the geometrical parameters of the bolometer region – specifically, a length (L_B) of 4 μm and a width (W_B) of 8 μm – was conducted by considering heating efficiency, back-reflection, and in-house fabrication capabilities. The systematic process of optimizing geometries with numerical simulations is detailed in [Supplementary Note 2](#). Figure 1b shows the simulated steady-state temperature distribution for the device designed with the final parameters. The input waveguide, having a width (W_{in}) of 2 μm , was designed to support only the fundamental transverse-electric (TE) mode. The incoming light was set to an optical power of 1 mW at a wavelength (λ) of 4.18 μm . As depicted in Fig. 1b, there is a significant temperature rise confined within the bolometer region. This localized heat generation is achieved by FCA within the p^+ Ge, which demonstrates the viability of an FCA-based thermalization process acting as a compact and efficient MIR absorber, even in the absence of resonance structures.

Figures 1c and 1d show the optical microscope and cross-sectional transmission electron microscopy (TEM) images, respectively, of the fabricated device on the Ge-OI photonic platform featuring a 500 nm-thick top Ge, a 2 μm -thick Y_2O_3 BOX, and a Si substrate. Here, the proposed waveguide-integrated PD incorporates a boron-doped p^+ Ge (bolometer region), a $\text{SiO}_2/\text{Al}_2\text{O}_3$ (20/25 nm) insulating layer stack, a bolometric material of $\text{TiO}_2/\text{Ti}/\text{TiO}_2$ (25/2/25 nm) tri-layer film, and a Ti/W (100/150 nm) metal electrode. The thickness of each layer in the bolometric material was carefully optimized (discussed in [Supplementary Fig. S6](#)). Additional characterizations, such as X-ray photoelectron spectroscopy (XPS) and X-ray diffraction (XRD), are detailed in [Supplementary Figs. S8 and S9](#), respectively. Energy-dispersive X-ray spectroscopy (EDS) elemental mapping (see [Supplementary Fig. S10](#)) confirms the successful deposition of each layer. Secondary-ion mass spectrometry (SIMS) depth profile analysis in Fig. 1e quantitatively reveals the impurity dopant concentration within the p^+ Ge region. To make full use of FCA in Ge, ion implantation was performed with a high dopant dose of $5 \times 10^{15} \text{ cm}^{-2}$, and the implant energy was carefully adjusted to 110 keV. This optimization contributes to exposing a larger fraction of the modal field to the absorbing medium with peak doping-concentration, aligning with the mode-field maximum and the projected range (R_p) of the implanted ions in the p^+ Ge.

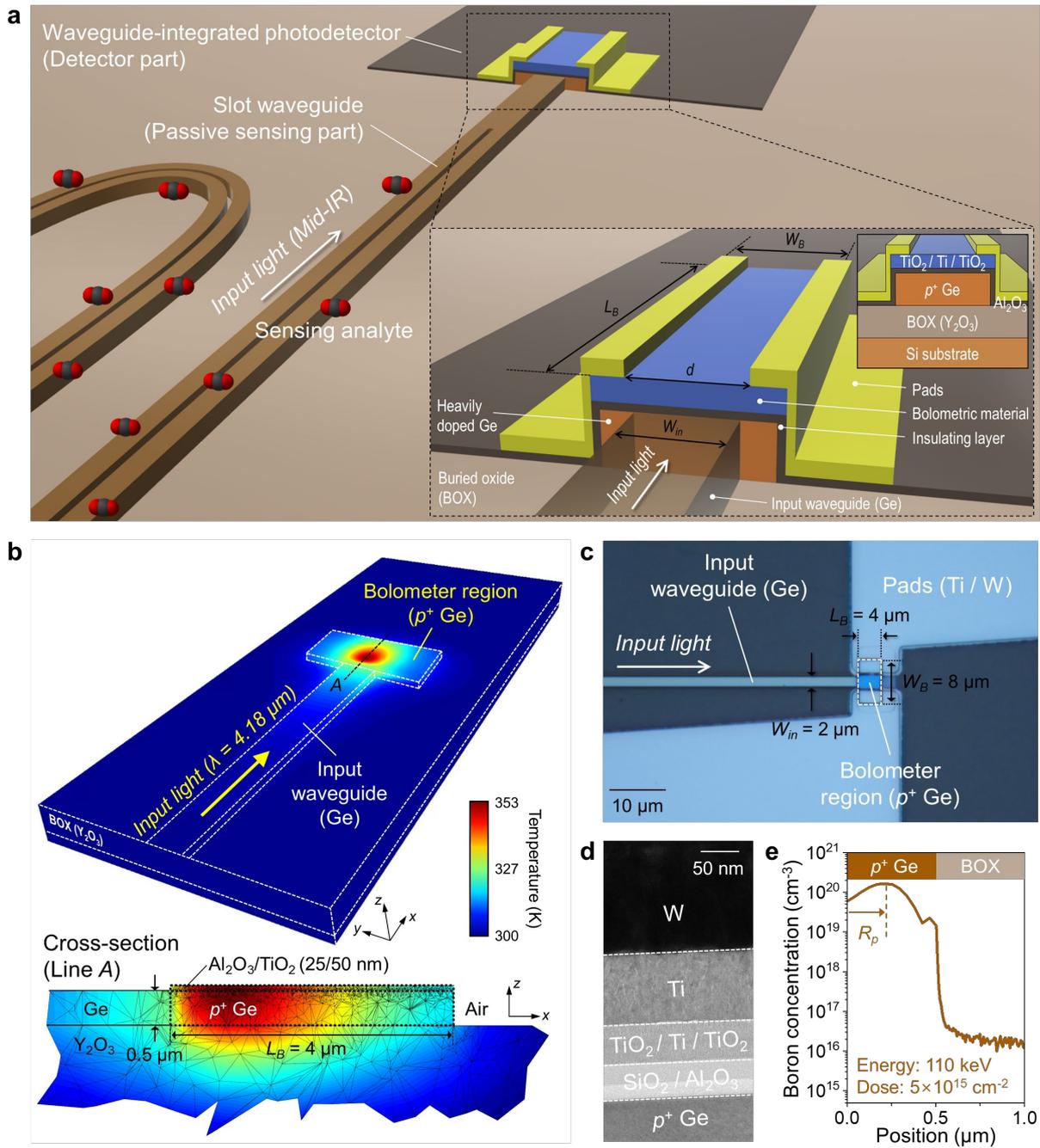


Figure 1. Structure of the proposed device. **a** Illustration of the MIR PIC-based sensor on the Ge-OI platform consisting of the sensing waveguide and photodetector. The zoom-in view shows the schematic of the proposed waveguide-integrated photodetector using the bolometric effect combined with FCA in Ge. **b** Heat simulation (Ansys Lumerical) results showing steady-state temperature distribution within the proposed photodetector ($W_B = 8 \mu\text{m}$, $L_B = 4 \mu\text{m}$) for an incoming light at $4.18 \mu\text{m}$ (1 mW). Doping concentration of p^+ Ge region was assumed as 10^{20}cm^{-3} . Background temperature was set to be 300 K. **c** Optical microscope image of the fabricated device. **d** Cross-sectional TEM image of the device including the electrode region. **e** SIMS depth profile analysis indicating the boron-doped p^+ Ge region. The implant energy and dopant dose were 110 keV and $5 \times 10^{15} \text{cm}^{-2}$, respectively.

Thermo-electrical characterization. We first investigated the temperature-dependent electrical properties. Figure 2a shows the current-voltage (I - V) curves from a voltage sweep ranging from -3.0 V to +3.0 V, with a 0.01-V interval, measured from 293 K to 363 K, limited by our Peltier-driven stage. A nearly-linear characteristics with Ohmic behavior between the bolometric

material and the electrode stack was obviously observed. Figure 2b plots the temperature-dependent current values at 3-V derived from the I - V curves, demonstrating a significant relationship with the temperature. Figure 2c presents the resistance-temperature (R - T) characteristics under constant-voltage mode, which can be modeled following equation to estimate the activation energy (ΔE):

$$R(T) = R_0 \exp\left(\frac{\Delta E}{k_B T}\right) \quad (2)$$

where $R(T)$ denotes the temperature-dependent electrical resistance, T is the absolute temperature, R_0 is a constant, and k_B is the Boltzmann constant. From Equation (2), ΔE is extracted from the slope of the Arrhenius plot ($\ln(R)$ vs. $1000/T$) shown in Fig. 2d, which was determined to be 0.315 eV within the measured temperature range. The temperature-dependent current modeling over a high-temperature range, based on the Arrhenius relationship by Equation (2), is described in the inset of Fig. 2b, revealing a rapid increase in electrical current with rising temperature.

To quantify the temperature dependence of the electrical resistance, temperature-coefficient of resistance (TCR), a crucial performance indicator for bolometric detectors, is introduced, which is defined as the derivative of resistance with respect to temperature,

$$\text{TCR} = \left(\frac{1}{R}\right)\left(\frac{dR}{dT}\right) = -\frac{\Delta E}{k_B T^2}. \quad (3)$$

Figure 2e shows the temperature-dependent TCR, as obtained by Equation (3). Here, our device achieved a TCR of -4.262 %/K at 293 K, the highest to date for waveguide-integrated PDs utilizing the bolometric effect, thus enhancing bolometric photodetection capabilities.

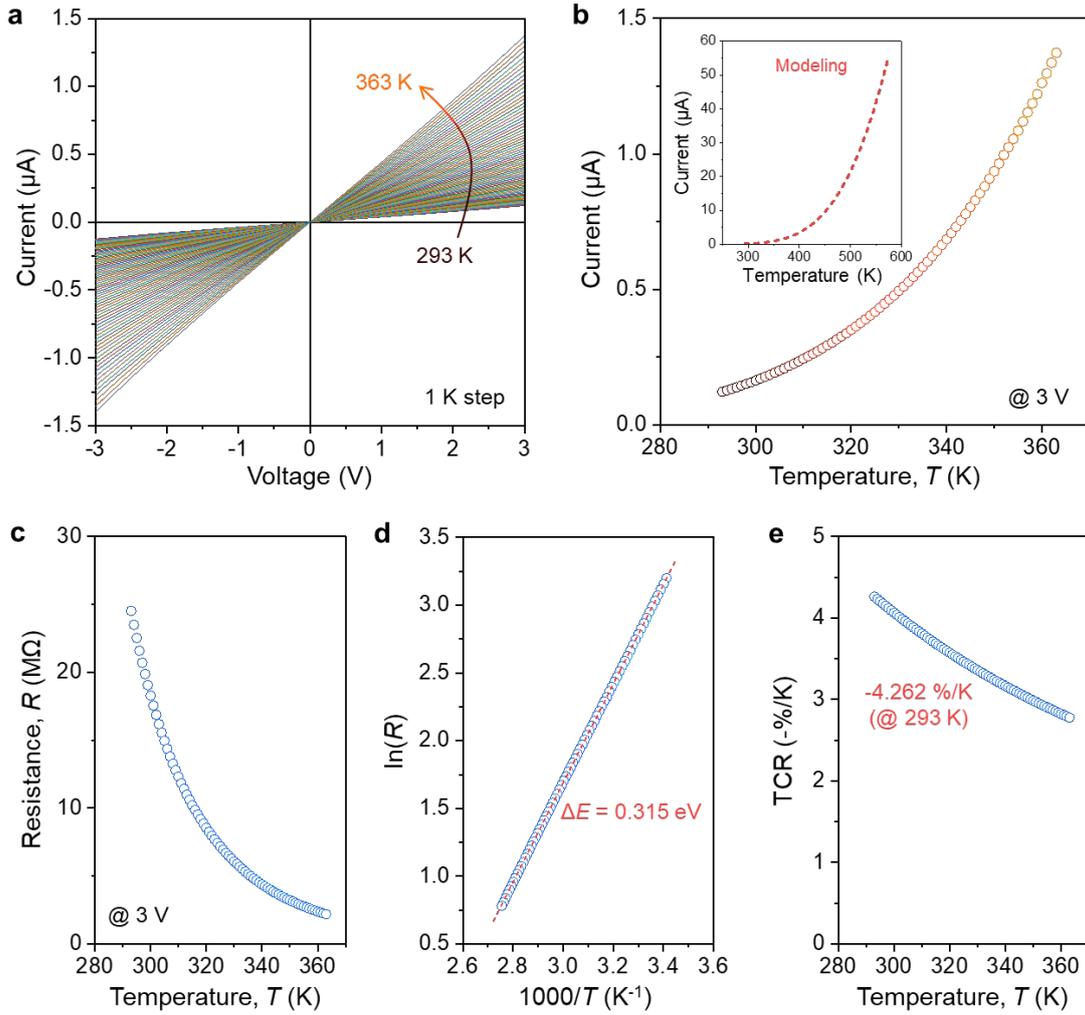


Figure 2. Thermo-electrical characteristics. **a** Current-voltage (I - V) curves measured from 293 K to 363 K (1 K step), controlled by a Peltier-driven stage with a 10-mV interval. **b** Temperature dependence of current values at a 3-V biasing. The inset indicates the modeled current values depending on the temperature, calculated from the Arrhenius equation. **c** Resistance-temperature (R - T) characteristics under a 3-V biasing, following the Arrhenius relationship. **d** Arrhenius plot [$\ln(R)$ vs. $1000/T$] with the activation energy (ΔE) calculated from the slope of the linear fit (red dashed line), indicating $\Delta E = 0.315$ eV. **e** TCR (-%/K) values depending on the temperature, showing -4.262 %/K at 293 K.

Photoresponse measurement. We now turn to explore the MIR photoresponse. The incident optical power coupled into the bolometer region was precisely calibrated, accounting for insertion losses from passive components with the assistance of an identical reference waveguide pattern without the detector part (see [Supplementary Fig. S7](#)). The un-illuminated I - V curve (dark state), plotted in the inset of Fig. 3a, revealed a dark current (I_{dark}) of 127.5 nA at 3-V bias. Figure 3a presents the optical power (P_{in}) dependence on the photocurrent ($I_{\text{ph}} = I_{\text{light}} - I_{\text{dark}}$) and the corresponding responsivity ($R = I_{\text{ph}} / P_{\text{in}}$) at 4.18 μm , under a 1 kHz chopping frequency. We highlight that our device achieved an R of 12.19 mA/W (from linear fitting at $P_{\text{in}} > 0.3$ mW), exceeding the previous state-of-the-art value in waveguide-integrated thermal-type PDs beyond 3 μm , which is 10 mA/W at 5.2 μm in graphene-based PD on ChG-on-CaF₂ waveguide using the PTE effect²⁸. A slight nonlinearity is observed at lower

P_{in} ranges, potentially attributed to variations in thermo-electrical properties and changes in both G_{th} and C_{th} with temperature. Additionally, we estimated the noise-equivalent power (NEP) by taking the ratio of the noise spectral density in dark state (see [Supplementary Note 5](#)) to the R of 12.19 mA at 4.18 μm , calculated as $3.4 \times 10^{-9} \text{ W/Hz}^{1/2}$ at 1 kHz. Here, this far exceeds that of previously reported waveguide-integrated MIR PD using the bolometric effect ($10.4 \mu\text{W/Hz}^{0.5}$ at 3.8 μm)²⁷ and is comparable to the PTE-based PD ($1.1 \text{ nW/Hz}^{0.5}$ at 5.2 μm)²⁸.

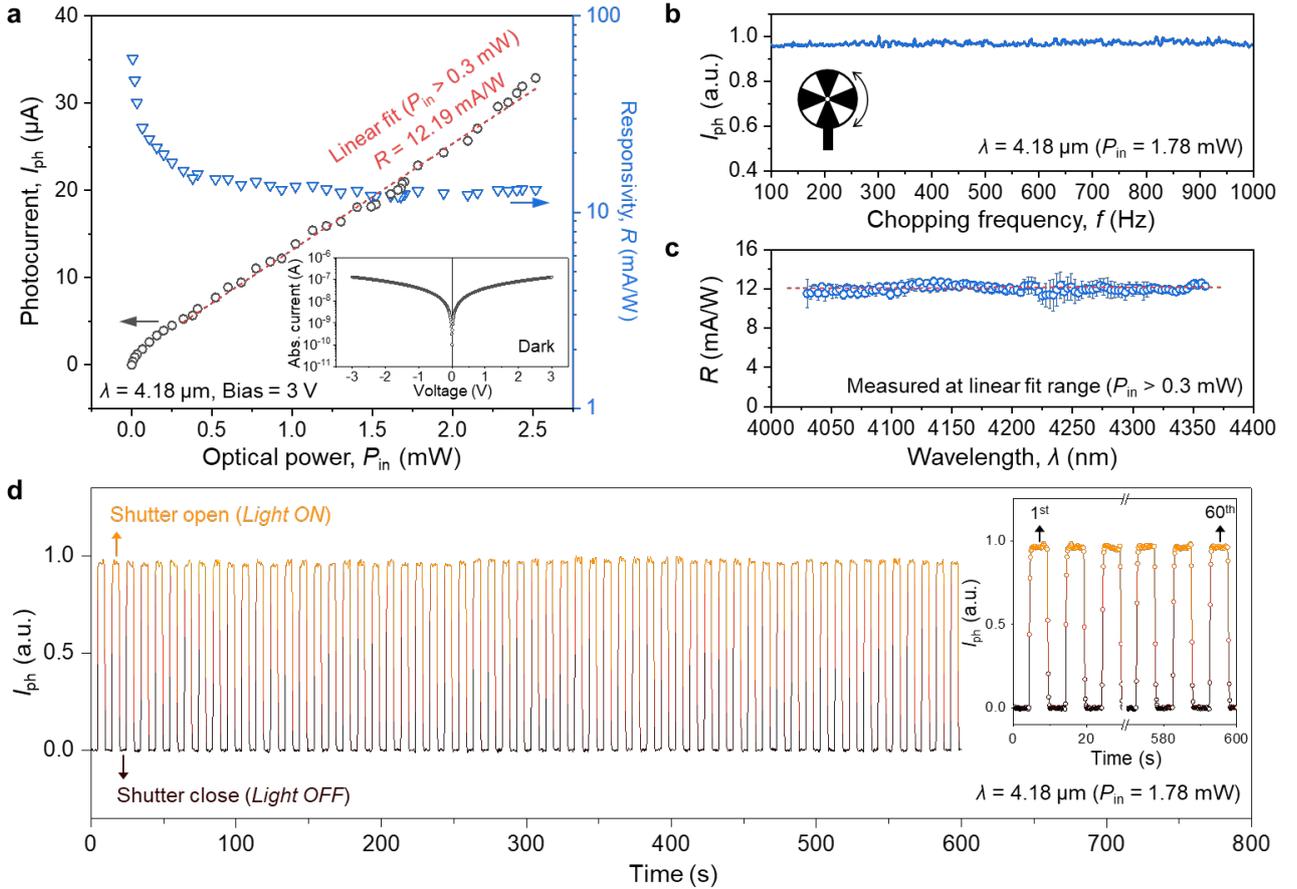


Figure 3. Photoresponse characterization. **a** Photocurrent as a function of incident optical power (P_{in}) toward bolometer region at a wavelength (λ) of 4.18 μm , showing a responsivity (R) of 12.19 mA/W from linear fitting ($P_{in} > 0.3 \text{ mW}$). The inset shows the I - V curve under dark condition. **b** Photoresponse under varying chopping frequencies. **c** Spectral response over the range of 4030–4360 nm. **d** Time stability measurement test of photoresponse during continuous ON/OFF cycles with a 10 seconds period, controlled by a beam shutter.

The frequency response was analyzed by varying the chopper frequency. As illustrated in Fig. 3b, our device showed stable performance with a nearly flat response up to 1 kHz (the limit of our setup). Although higher bandwidth might be beneficial, it is not a major concern in most spectroscopy applications – unlike in telecommunications and data communications – suggesting that our device is sufficiently robust for MIR lab-on-a-chip systems. We also evaluated the spectral response in the

MIR band ranging from 4030 to 4360 nm. During the measurement, the P_{in} was maintained within the linear fit region ($P_{in} > 0.3$ mW). Our device exhibited a broadband photoresponse with an R of ~ 12 mA/W across the entire measurable range without any cutoff wavelengths. Lastly, we assessed the long-term stability with switching behavior, a key parameter for evaluating PDs. Notably, as depicted in Fig. 3d, highly stable and repeatable photocurrent generation was observed without noticeable performance degradation throughout the measurements. Here, we note that the response times were constrained by the open/close time of the beam shutter.

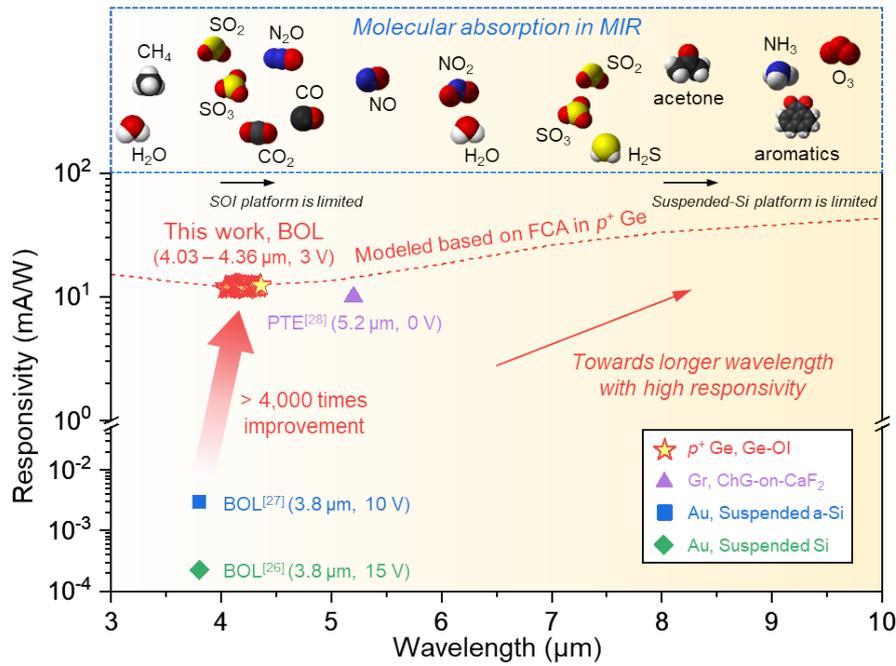


Figure 4. Benchmark. Performance comparison of waveguide-integrated thermal-type PDs operating beyond 3 μm . The red dotted line represents the responsivity modeling based on FCA in Ge, aligned with our experimental results. Our approach, leveraging the FCA-induced heating mechanism and the Ge-OI platform, can cover the entire MIR spectrum for spectroscopic analysis of numerous biochemical molecules. For each reference, the mechanism of thermal detection, the absorbing medium, and the waveguide platform are indicated. BOL, bolometric; PTE, photothermoelectric; ChG, chalcogenide glass; Gr, graphene. References [26] Wu, Y. et al., *ACS Photonics* **6** (2019); [27] Wu, Y. et al., *Opt. Lett.* **46** (2021); [28] Goldstein, J. et al., *Nat. Commun.* **13** (2022).

We have comprehensively compared our device's performance with that of previously reported MIR waveguide-integrated thermal-type PDs, as shown in Fig. 4. Our device exhibits a broad responsivity of ~ 12 mA/W, the highest among its counterparts, achieving an improvement of over 4,000 times compared to the previous waveguide PD using the bolometric effect²⁷. Furthermore, there have been no demonstrations of waveguide-integrated thermal-type PDs beyond 5.2 μm . Traditional Si-based photonics platforms, such as Si-on-insulator (SOI) with a limit of ~ 4 μm and suspended-Si with ~ 8 μm , inevitably encounter wavelength limitations due to the intrinsic material absorption of SiO_2 and Si in the MIR range³⁶. Here,

by leveraging the FCA-induced heating process on the Ge-OI platform that provides a broad transparency window, our approach can be widely utilized across much shorter or longer wavelength ranges in the MIR spectrum, offering significant potential for spectroscopic analysis of numerous biochemical molecules (shown in Fig. 4) without wavelength constraints. The responsivity modeling, based on FCA in Ge³⁰ and normalized with our experimental results, is presented in Fig. 4 (red dotted line). Detailed performance characteristics are summarized in [Supplementary Note 9](#).

Sensing demonstration. To demonstrate the label-free light–analyte interaction capabilities of our MIR PIC-based sensing platform, we arranged a 5-mm-long slot waveguide with our waveguide-integrated PD on a single Ge-OI chip, as shown in Fig. 5a. Efficient mode conversion was facilitated by strip-to-slot and slot-to-strip mode converters³⁴ positioned at the entry and exit points of the slot waveguide (detailed in [Supplementary Note 8](#)), respectively, as depicted in the optical microscope and scanning electron microscope (SEM) images in Fig. 5b. The slot waveguide, designed for high confinement within an air-clad, featured geometrical parameters of 1.8 μm width (W), 0.2 μm slot gap (G), and 500 nm height (H)³⁴, as shown in the cross-sectional SEM image in Fig. 5c, highlighting the well-defined slot region where the light–analyte interaction occurs.

Here, CO₂, a major greenhouse gas contributing to global warming³⁷, was selected as the target analyte with a strong absorption coefficient at 4.23 μm ³⁸. Under the continuous-wave (CW) operation at 4.23 μm , changes in CO₂ gas concentration were detected by the photocurrent signal from our detector while simultaneously monitoring the actual CO₂ levels using a commercial gas sensor placed near the device inside the chamber. Operation conditions were maintained at 3 V and 1 kHz for biasing and chopping frequency, respectively. Figure 5d presents the normalized photocurrent signal depending on the CO₂ concentration, which exhibits a downward trend as expected from the absorption spectroscopy technique, achieving a sensitivity of 0.0696 %/ppm through linear fitting. Additionally, to assess the repeatability of our optical sensing, we cycled the CO₂ valve under nitrogen (N₂) gas purging, varying the CO₂ concentration between 100 and 250 ppm. As indicated in Fig. 5e, the photocurrent signal varied clearly and repeatably with the CO₂ levels, exhibiting no memory effects. It should be noted that the response times were constrained by our experimental setup for both injecting and removing CO₂ gas within the chamber.

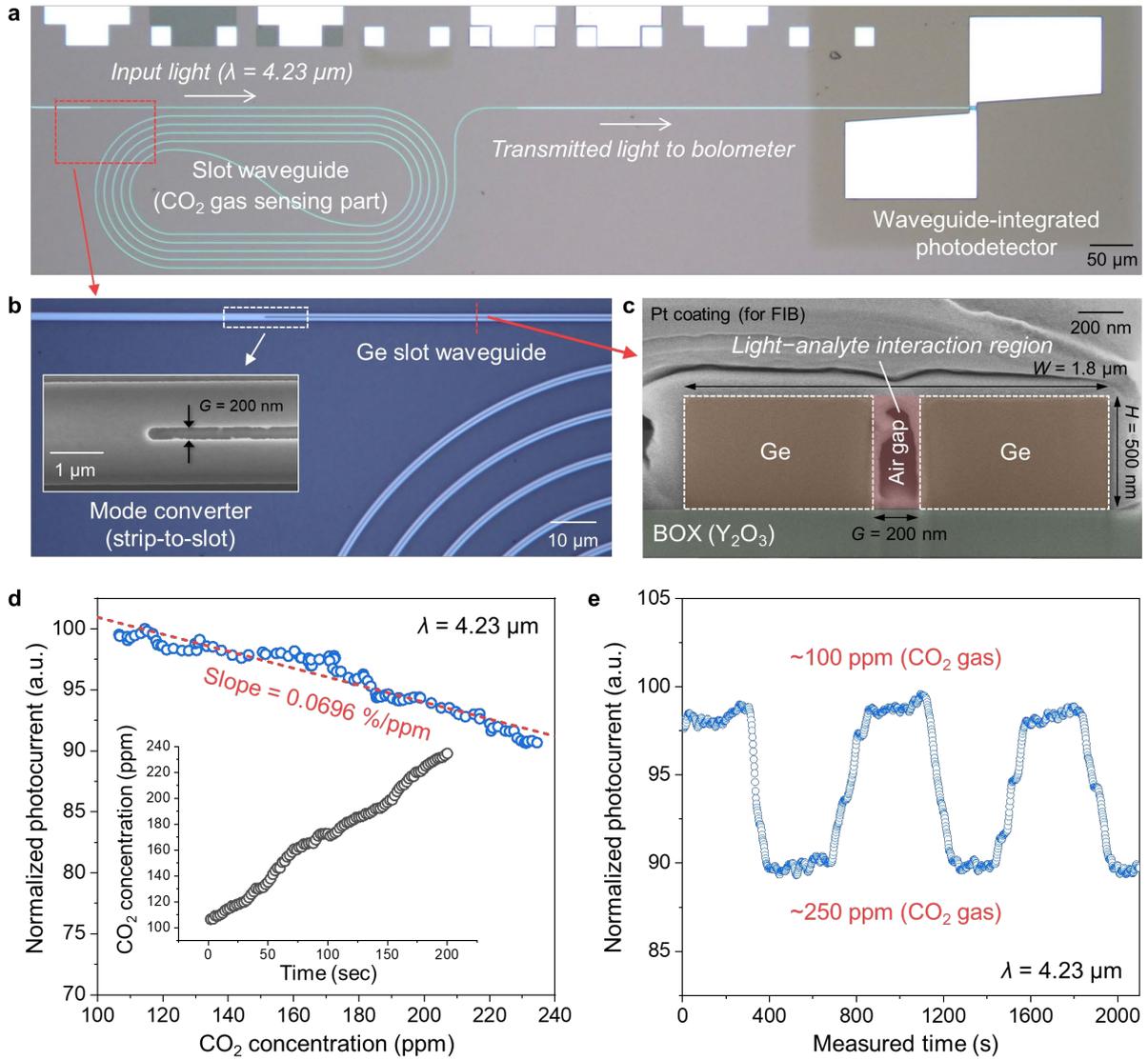


Figure 5. Optical sensing demonstration. **a** Optical microscope image of the integrated photodetector connected with slot waveguide on the Ge-OI platform. **b** Magnified optical microscope image of the Ge slot waveguide. The inset shows the SEM image of the strip-to-slot mode converter. **c** Cross-sectional SEM image showing the slot waveguide with a width (W) of $1.8 \mu\text{m}$ and a gap (G) of 200 nm where the light-analyte interaction occurs. **d** Normalized photocurrent at wavelength of $4.23 \mu\text{m}$ and 3-V biasing, measured under varying CO₂ gas concentration. The inset shows the CO₂ concentration monitored by a commercial CO₂ gas sensor during the photocurrent measurement. **e** Repeatability test of photocurrent at varying CO₂ concentrations. All measurements were performed at room temperature.

Discussion

In the field of integrated photonics, unlike in imaging optics, thermal detection mechanisms have yet to be fully harnessed. As indicated in Fig. 4, there have been very few experimental demonstrations to date, which might be attributed to the challenges of introducing thermal detection mechanisms into MIR waveguide platforms. Here, we present a straightforward, highly CMOS-compatible method for realizing thermal detection within waveguide structures. The key idea of our strategy is primarily based on the FCA-induced thermalization process in heavily doped Ge, providing as a viable solution for light-to-

heat conversion in MIR absorption without relying on exotic materials in CMOS or hybrid integrations. The ion implantation process is a well-established technique in current semiconductor technologies, enabling fabrication ease, cost-effectiveness, and scalability. Additionally, this approach can be readily adopted into various Si- or Ge-based MIR photonic platforms, including SOI³⁹, suspended-Si³⁶, Ge-on-Si (GOS)⁴⁰, suspended-Ge⁴¹, Ge-on-SOI⁴², and Ge-OI^{34,35}. Furthermore, as bolometry with FCA in Ge is not wavelength-specific, the operational range is extendable across the entire MIR spectrum without encountering cutoff regions.

We have achieved outstanding bolometric photoresponse characteristics through several strategic interventions: enhancing FCA-induced heating in Ge, optimizing device geometries, and improving thermo-electrical properties. Here, increasing the bias voltage may bring into reach further high photoresponsivity up to the breakdown regime at the expense of a rise in the dark current level (detailed in [Supplementary Note 6](#)). Additionally, we can potentially push the photoresponse to a much higher level through various strategies, such as scaling down the width of bolometer region and implementing a top-contact electrode scheme above the dielectric cladding with via plugs⁴³, improving heat confinement within the absorbing medium. Moreover, thermal-isolation designs, such as air-trench or free-standing structures underneath the p^+ Ge region, are advantageous for boosting heating efficiency and mitigating thermal crosstalk between adjacent detectors in an array configuration, albeit at the cost of increased response time. Regarding the bolometric material of the TiO₂/Ti/TiO₂ tri-layer film stack, engineering the thickness of each layer and the annealing condition provides the flexibility to tailor electrical resistivity and thermo-electrical properties to meet the requirements of diverse spectroscopy applications³¹.

We have successfully demonstrated label-free light-analyte interaction of CO₂ molecules using our PIC-based sensing system on the Ge-OI platform. While there are few reports of molecule detection utilizing MIR waveguide-based sensors with monolithic integration of detectors at room temperature^{16,44}, our work is pioneering in realizing CO₂ sensing. Moreover, given the ultra-broadband photoresponse characteristics of our approach, we envision the full potential of broad applicability in MIR spectroscopic sensing of various biochemical molecules, as well as real-time detection of multiple analytes, leveraging the label-free nature of the absorption spectroscopy method. Integrating MIR sources, such as interband cascade lasers (ICL)⁴⁵ and quantum cascade lasers (QCL)⁴⁶, could further enhance our approach, paving the way for a fully integrated MIR PIC-based lab-on-a-chip system. Furthermore, employing computational spectroscopy techniques, particularly through disordered structures^{9,47,48}, could serve as a strategy to minimize system footprint and power consumption while improving robust and agile multiplexed-detection capabilities.

Materials and methods

Simulation. The numerical simulations were conducted using the commercial simulation software packages of Ansys Lumerical, specifically the 3D-FDTD (finite-difference time-domain) and HEAT solvers. The Ge-OI structure was designed with a 500 nm-thick top layer of Ge, a 2 μm -thick Y_2O_3 BOX and a Si substrate. For simplicity in analysis, the bolometric material was modeled as a 50 nm-thick TiO_2 layer. For the steady-state thermal simulation, the heat source was imported from the absorption data obtained by the 3D-FDTD solver. The background temperature was set at 300 K. A doping concentration in the p^+ Ge region was assumed to be 10^{20} cm^{-3} . Changes in refractive index and absorption coefficient were calculated based on the literature³⁰ and these values at specific wavelengths were approximated using linear interpolation.

Device fabrication. The fabrication process flow of the waveguide-integrated PD using the bolometric effect on the Ge-OI platform is illustrated in [Supplementary Note 3](#). It began with the fabrication of a Ge-OI wafer, which features a 500 nm-thick top Ge, a 2 μm -thick Y_2O_3 buried oxide layer, and a Si substrate. We first prepared two types of wafers: (i) the acceptor wafer, which is a Si(100) substrate, and (ii) the donor wafer, comprising a Ge(100)/ $\text{Si}_{0.5}\text{Ge}_{0.5}$ /Ge strain relaxed buffer (SRB) layer stack on Si(100) substrate with a thickness of 500 nm, 10 nm, and 900 nm, respectively, grown by the metal-organic chemical vapor deposition (MOCVD) method. We introduced the $\text{Si}_{0.5}\text{Ge}_{0.5}$ and Ge SRB layers, thereby obtaining a high-quality Ge epitaxial layer with a reduction of lattice mismatch between Si and Ge. We then deposited a 1 μm -thick Y_2O_3 layer on both donor and acceptor wafers using the radio-frequency (RF) magnetron sputtering method at 150 $^\circ\text{C}$, ensuring crack-free oxide films. Prior to the direct wafer bonding (DWB) process, we conducted chemical mechanical polishing (CMP) with a silica slurry to planarize the surfaces. As a result, we achieved a surface roughness of approximately 0.6 nm (root-mean-square), as measured by atomic force microscopy (AFM) analysis, which was sufficiently clean and smooth for DWB. After the surface cleaning and O_2 plasma treatment, we performed the DWB procedure, followed by the removal of the Si substrate with the sequential processes of mechanical grinding and selective etching using a diluted tetramethylammonium hydroxide (TMAH) solution at 90 $^\circ\text{C}$. The Ge SRB and $\text{Si}_{0.5}\text{Ge}_{0.5}$ layers were etched away using the APM solution (ammonia hydroxide-hydrogen peroxide water mixture) and the diluted TMAH solution, respectively, resulting in the successful fabrication of the Ge-OI wafer. We then performed electron-beam (e-beam) lithography (NanoBeam Ltd, nB5) with a negative e-beam resist (AR-N 7520) to pattern passive devices; afterwards, an inductively coupled plasma reactive ion etching (ICP-RIE) process (15 sccm C_4F_8 and 40 sccm SF_6 at a pressure of 25 mTorr, ICP power of 600 W, and RF power of 50 W) was implemented to realize an etching depth of 500 nm, followed by the removal of the e-beam resist in acetone. Prior to ion implantation for forming a p^+ Ge region, we deposited a 20 nm-thick dielectric SiO_2 layer at 150 $^\circ\text{C}$ by atomic layer deposition (ALD) to protect the surface of Ge layer from potential contamination or damage, which can occur due to the impact of high-energy ions and the removal of photoresist (PR) mask for doping region definition. Subsequently, the ion (boron) implantation process was conducted with an implant energy of 110 keV and a dopant dose of $5 \times 10^{15} \text{ cm}^{-2}$, followed by activation annealing at 350 $^\circ\text{C}$ in an N_2 ambient for 3 min. A 25 nm-thick Al_2O_3 insulating layer was grown with ALD at 170 $^\circ\text{C}$ to eliminate undesirable leakage currents through the Ge layer. A wet etching process using a diluted hydrofluoric acid (HF) solution was then conducted to selectively remove the SiO_2 and Al_2O_3 oxide layers, while preserving the area surrounding the p^+ Ge region. Subsequently, the bolometric material, consisting of a $\text{TiO}_2/\text{Ti}/\text{TiO}_2$ (25/2/25 nm) tri-layer film stack, was sequentially deposited with e-beam evaporation, followed by an acetone lift-off process. Finally, we formed an electrode stack of Ti/W (100/150 nm) with a spacing of $\sim 2 \mu\text{m}$ through e-beam evaporation and direct current (DC) sputtering, respectively, followed by lift-off using an acetone soak.

Electrical characterization. The electrical properties of the fabricated device were characterized using a semiconductor parameter analyzer (Keithley 4200A-SCS) in a four-point probe system equipped with a thermoelectric Peltier-driven stage to precisely control of the background temperature. For DC current-voltage (I - V) characterization, the source measure units (SMUs) were utilized to perform a voltage sweep while simultaneously measuring the current with high resolution and accuracy. For low-frequency noise (LFN) analysis, the pulse measure units (PMUs) were employed to capture time-varying current fluctuations, followed by fast Fourier transform (FFT) calculations to analyze the data.

Photoresponse and gas sensing characterization. We built an in-house measurement system for photoresponse and gas sensing, as illustrated in Fig. 6. A tunable QCL source (Daylight Solutions MIRcat-QT-2100) under CW operation mode was modulated by a chopper (Scitec Instruments) with a specific reference frequency. Since our grating couplers (GCs) are optimized for the TE-mode³⁴, we employed a polarizer to maximize optical coupling efficiency. After that, the input light was

launched into an indium fluoride (InF_3) single-mode optical fiber (Thorlabs) through an aspheric lens with a fiber holder. Alignment between the cleaved InF_3 fiber facet and the fabricated device was precisely achieved using a goniometer and three-axis translational stages with a charge-coupled device (CCD) camera. For the characterization of the passive components, the output light was directed into another InF_3 optical fiber and subsequently collimated into a mercury cadmium telluride (MCT) detector (VIGO systems PVI-4TE-5). The amount of coupled optical power was calibrated using an external MCT photodiode power sensor (Thorlabs S180C). Propagation losses of strip and slot waveguides were analyzed using the cut-back method, as detailed in [Supplementary Note 7](#). During photoresponse measurements, a programmable current amplifier (Keithley 428-PROG) with two probe contacts was used to apply bias voltage, and the resulting photoresponse signals were monitored on a lock-in amplifier (Stanford Research Systems SR830) for the signal-to-noise (SNR) ratio enhancement. For time stability measurements, a beam shutter (Thorlabs SHB1T) controlled by a function generator (FG, Tektronix AFG3022B) was implemented to turn the coupled light on and off during CW operation. All photoresponse measurements were conducted within an acrylic chamber under a pure N_2 gas purging state to mitigate any undesirable impact on CO_2 gas absorption from the atmospheric environment. For optical gas sensing demonstrations, CO_2 concentrations were regulated using a mass flow meter with a diluting pure N_2 gas into the acrylic chamber, which were precisely calibrated by a commercial CO_2 gas sensor (Sensirion AG). Here, the lowest achievable CO_2 concentration within the acrylic chamber was around 100 ppm, limited by the capabilities of our setup under an N_2 gas purging state. All measurements were carried out at room temperature.

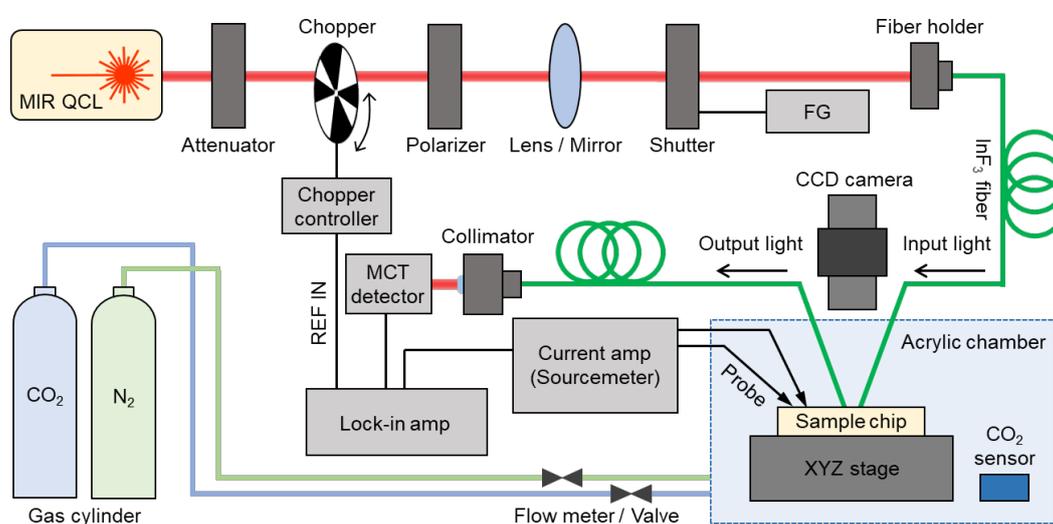


Figure 6. Schematic of photoresponse and gas sensing measurement setup. MIR, mid-infrared; QCL, quantum cascade laser; CCD, charge-coupled device, FG, function generator; MCT, mercury cadmium telluride.

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J. Shim proposed the idea, conducted the numerical simulations, and performed the measurements. J. Shim, J. Lim and I. Kim fabricated the device and built the experimental setup. J. Jeong, B. H. Kim, S. K. Kim, D.-M. Geum, and S. H. Kim contributed to the data analysis and discussion. S. H. Kim supervised the project. All authors contributed to the interpretation of results and prepared the manuscript.

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Data availability

All data that support the findings of this work are available within the paper. Additional data are available from the corresponding authors upon request.

Competing interests

The authors declare that they have no conflict of interest.

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Supplementary Information: Room-temperature waveguide-integrated photodetector using bolometric effect for mid-infrared spectroscopy applications

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Supplementary Note 1. Free-carrier absorption (FCA) in Ge

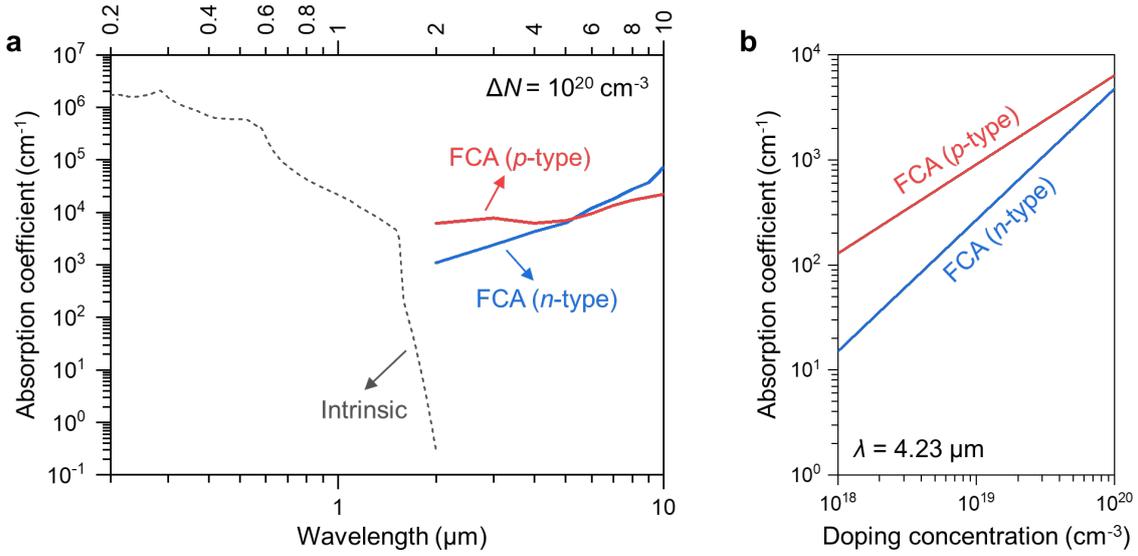


Fig. S1. FCA in Ge. **a** Absorption coefficients in Ge for intrinsic absorption and for FCA in both *n*- and *p*-type Ge with a doping (impurity) concentration (ΔN) of 10^{20} cm^{-3} depending on the wavelengths. **b** Comparison of the calculated FCA coefficients as a function of the doping concentration for *n*- and *p*-type Ge at a wavelength (λ) of $4.23 \text{ }\mu\text{m}$. The absorption coefficients for FCA in Ge are calculated based on the literature¹.

The free-carrier absorption (FCA) is a process where free carriers, i.e., free electrons and free holes, absorb the incoming photon energy, leading to non-radiative carrier transition with the thermalization process^{1,2}. There are two types of FCA in Ge: FCA in *n*-type Ge and FCA in *p*-type Ge, each corresponding to the absorption attributed to the free electrons and free holes, respectively. The absorption coefficients in Ge for intrinsic absorption (band-to-band absorption) and FCA are plotted in Fig. S1a. The doping (impurity) concentration (ΔN) is assumed to be 10^{20} cm^{-3} . The intrinsic absorption of Ge is negligible beyond the wavelength of $\sim 1.9 \text{ }\mu\text{m}$; however, FCA becomes increasingly significant beyond the bandgap energies. Furthermore, FCA in Ge shows a clear trend of increase with the wavelength of light, highlighting the importance of our approach for broadband mid-infrared (MIR) photodetection – even much higher photoresponse at longer wavelengths – within the waveguide structures on the Ge-on-insulator (Ge-OI) platform. Figure S1b represents the absorption coefficients of FCA for *n*- and *p*-type Ge depending on the doping concentration at the wavelength of $4.23 \text{ }\mu\text{m}$, chosen for the carbon dioxide (CO_2) gas sensing demonstration in this work. As shown in Fig. S1b, FCA is more pronounced in *p*-type doped Ge compared to *n*-type. Consequently, we selected *p*-type doping to maximize the FCA-induced heating process in our detector.

Supplementary Note 2. Optimizing device geometries

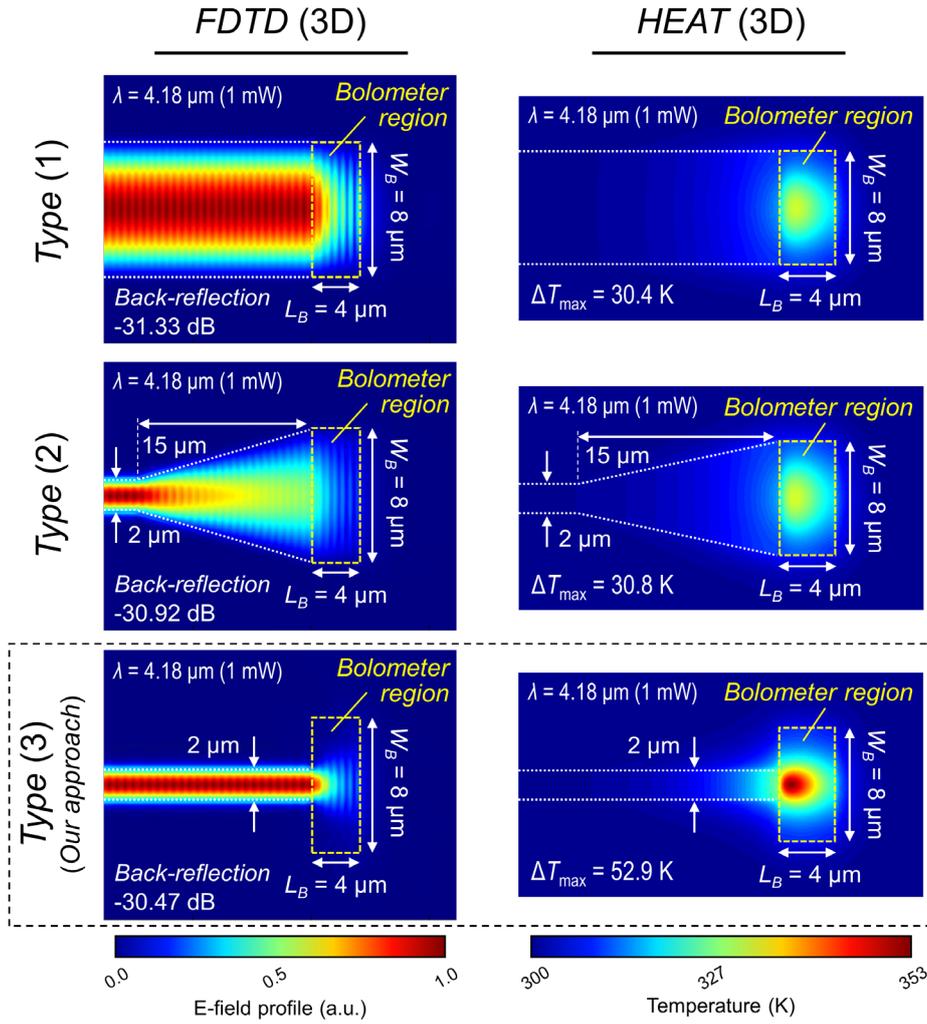


Fig. S2. Optimization of waveguide-to-bolometer interfacing geometries. The amount of back-reflection and FCA-induced heating efficiency was obtained through numerical simulations based on different interfacing geometries. Three device configurations were evaluated: Type (1) features a conventional structure, Type (2) incorporates a tapered structure, and Type (3) – our approach – utilizes an abrupt structure.

The optimization process of device geometries was conducted by numerical simulations of 3D-FDTD and HEAT solvers (Ansys Lumerical). We first introduced a terminated-waveguide structure, in which the input waveguide is terminated after the bolometer region (p^+ Ge region). Furthermore, we carefully considered the waveguide-to-bolometer interfacing geometry. Figure S2 describes a comparative analysis of three device configurations depending on the interfacing geometries: type (1) – conventional structure, type (2) – tapered structure, and type (3) – abrupt structure (our approach). An input light of 1 mW at 4.18 μm was assumed to support only the fundamental transverse-electric (TE) mode. Here, we primarily considered the amount of back-reflection and the FCA-induced heating efficiency. Type (1) illustrates a conventional waveguide with a uniform width leading directly into the bolometer region, which shows a back-reflection of -31.33 dB and a maximum temperature increase (ΔT_{max}) of 30.4 K. Type (2) depicts a tapered waveguide structure that gradually widens towards the bolometer region, resulting in a back-reflection of -30.92 dB and a ΔT_{max} of 30.8 K. Type (3) represents an abrupt transition

design with a narrow waveguide expanding suddenly to the relatively wider bolometer region, producing a similar lower back-reflection of -30.47 dB and a notably higher ΔT_{\max} of 52.9 K compared with other approaches. Consequently, we opted for the type (3) – abrupt structure – as our approach for enhanced FCA-induced heating performance with reasonable amount of back-reflection.

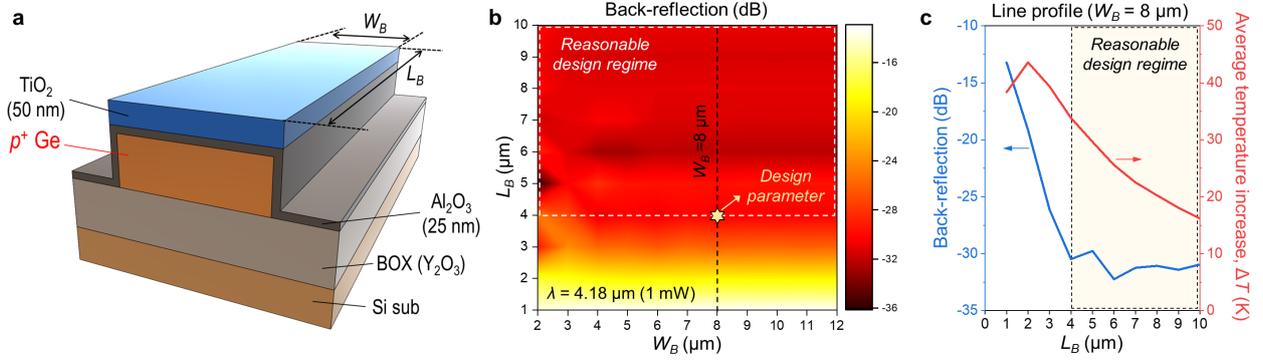


Fig. S3. Optimization of geometrical parameters of the bolometer region. **a** Schematic of the device structure for simulations. **b** Simulated contour map showing geometry-dependent back-reflection across varying L_B and W_B of the bolometer region. **c** Line profiles of both back-reflection and average temperature increase (ΔT) within the bolometer region as L_B varies for a fixed W_B of 8 μm .

Figure S3 presents the simulation results used to determine the optimal geometrical parameters of the bolometer region. A schematic of the simulated device structure is illustrated in Fig. S3a. For these simulations, we explored a wide range of lengths (L_B) and widths (W_B) for the bolometer region, while the width of an input waveguide (W_{in}) leading to the bolometer region was fixed at 2 μm . We first evaluated back-reflection, which can cause unwanted ripples that deteriorate the overall noise characteristics of the sensing system. Figure S3b represents a simulated contour map that shows the geometry-dependent back-reflection. At smaller L_B values, relatively higher back-reflection occurs due to insufficient light absorption in the bolometer region, while changes in W_B have little impact. As shown in Fig. S3b, an L_B greater than 4 μm is preferable, as it ensures back-reflection remains below approximately -30 dB, indicated by a white dotted line and considered within a reasonable design regime. Figure S3c depicts the line profiles of both back-reflection and average temperature increase (ΔT) within the bolometer region, as L_B varies for a W_B of 8 μm . Although smaller W_B could potentially enhance heat confinement, a width of 8 μm was chosen due to alignment tolerance constraints in subsequent in-house fabrication steps. Additionally, ΔT was calculated within the bolometer region for a central width of 2 μm , corresponding to the spacing of electrodes, due to the minor amount of transfer length between the prepared bolometric material and electrode stack. As shown in Fig. S3c, we finally selected an L_B of 4 μm and a W_B of 8 μm to achieve the highest ΔT within the reasonable design regime. It is important to note that the geometrical parameters of the bolometer region can be tailored based on the specific application requirements.

Supplementary Note 3. Fabrication process flow

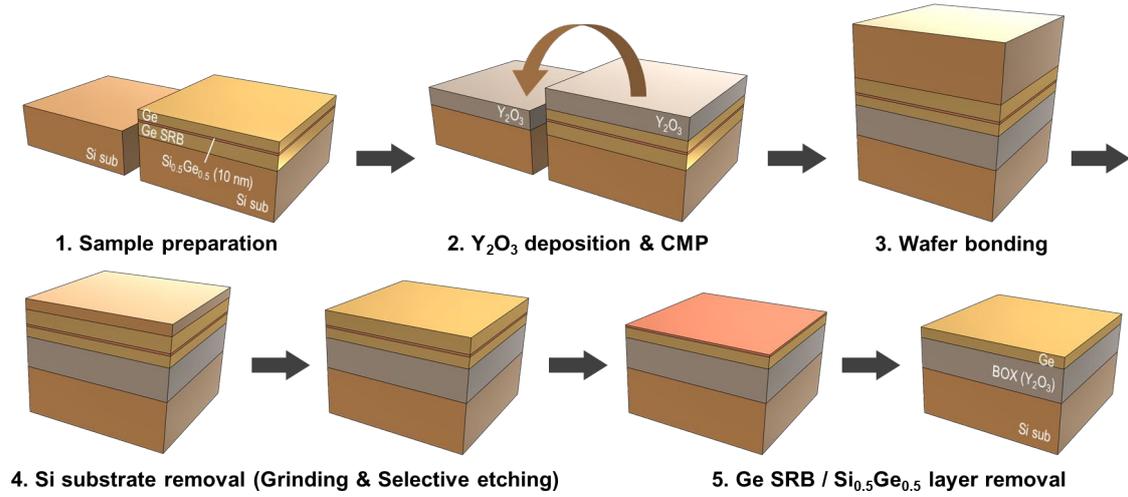


Fig. S4. Fabrication process flow of the Ge-OI photonic platform using direct wafer bonding (DWB) technique. SRB, strain relaxed buffer; BOX, buried oxide; CMP, chemical mechanical polishing.

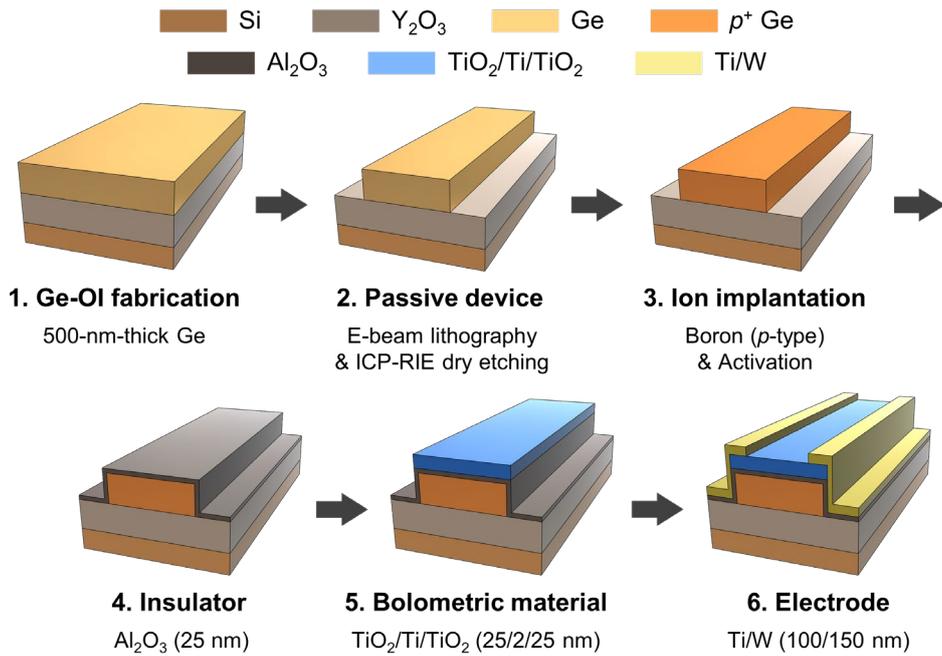


Fig. S5. Fabrication process flow of the proposed MIR waveguide-integrated PD on a Ge-OI platform. ICP-RIE, inductively coupled plasma reactive ion etching.

Figures S4 and S5 summarize the fabrication process flow of the proposed MIR waveguide-integrated photodetector (PD) on the Ge-OI platform using the bolometric effect with FCA process.

Supplementary Note 4. Device characterization

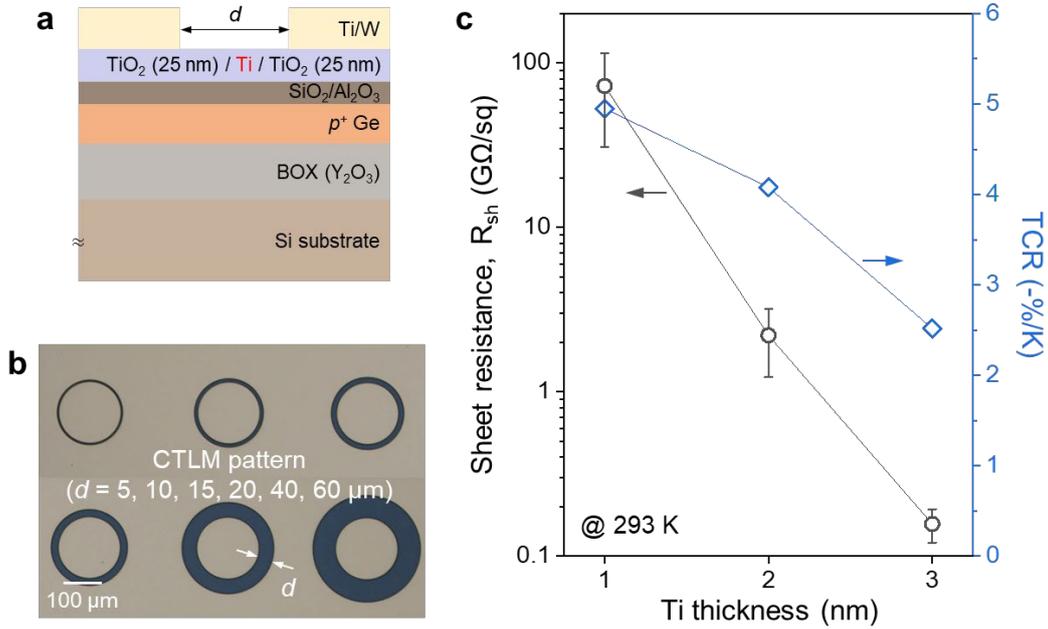


Fig. S6. Optimization of bolometric material. **a** Schematic of the device structure for the CTLM patterns. **b** Optical microscope image of the fabricated CTLM patterns. **c** Variation in sheet resistance (Ω/sq) and TCR (-%/K) depending on the thickness of the metallic Ti layer.

To optimize the thermo-electrical properties of the bolometric material in the $TiO_2/Ti/TiO_2$ tri-layer film, we fabricated the test devices with varying thickness of the metallic Ti layer. Figure S6a illustrates the schematic of these devices, which feature circular transmission line method (CTLM) patterns with spacings (d) of 5, 10, 15, 20, 40, and 60 μm , as depicted in the optical microscope image in Fig. S6b. For simplicity, the thickness of the upper and lower TiO_2 film was maintained at 25 nm, while the thickness of metallic Ti layer varied from 1 to 3 nm. The thickness of the other layers was kept consistent with those used in our waveguide-integrated photodetector. As demonstrated in Fig. S6c, the extracted sheet resistance (R_{sh}) values from the CTLM patterns at 293 K exhibit a clear downward trend as the thickness of the metallic Ti layer increases. Moreover, the temperature-coefficient of resistance (TCR) values, calculated from the temperature-dependent R_{sh} values, show a correlation with the R_{sh} values. Further detailed analysis can be found in our previous work³. It is important to note that this approach allows us to tailor the thermo-electrical properties of the bolometric material to meet specific application requirements. Here, we selected a 2 nm thickness for the metallic Ti layer to achieve an optimal balance of electrical resistance and high TCR value in our waveguide-integrated photodetector.

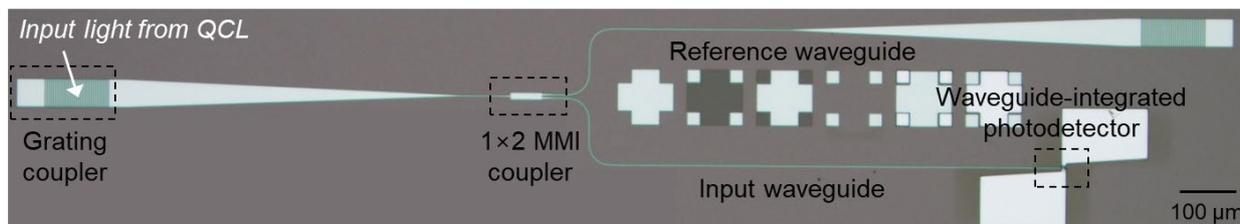


Fig. S7. Optical microscope image of the fabricated device with the reference waveguide pattern. QCL, quantum cascade lasers; MMI, multi-mode interference.

Figure S7 shows an optical microscope image of the fabricated waveguide-integrated photodetector with the reference waveguide structure, which was utilized to assist the optical alignment of fiber-optic coupling and to precisely calculate the optical power coupled into the bolometer region.

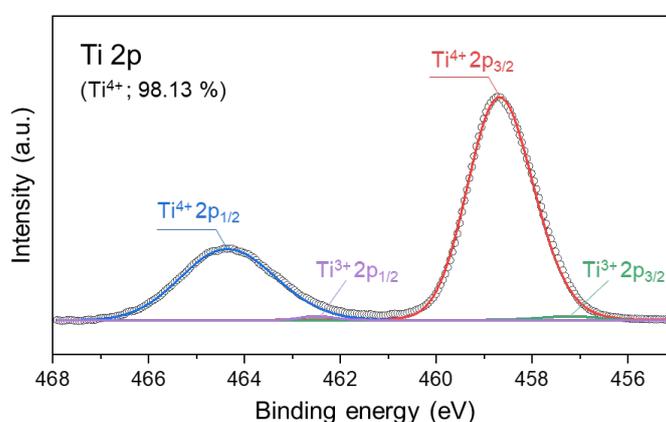


Fig. S8. XPS analysis of the TiO₂ thin film. The 25 nm-thick TiO₂ thin film predominantly consists of Ti⁴⁺ states.

To obtain comprehensive insights into the chemical bonding states and composition of the bolometric material, X-ray photoelectron spectroscopy (XPS) analysis was performed using the Thermo Scientific K-Alpha model at KAIST Analysis Center for Research Advancement (KARA). This analysis employed a monochromatic Al K α X-ray source to identify the chemical states. Calibration of the energy axis was achieved using the C 1s reference peak. Prior to analysis, the surface of the 25 nm TiO₂ thin film was cleaned by sputter-cleaning with an Ar⁺ ion beam (~5 nm depth) to prevent the effects of surface contaminants on the XPS results. Figure S8 shows the detailed Ti 2p XPS spectra. Deconvolution of these spectra was performed with reference⁴ to determine the relative proportions of each valence state. The analysis, as shown in Figure S8, indicated that the TiO₂ thin film predominantly consists of Ti⁴⁺ states (98.13%), with a minor presence of Ti³⁺ states.

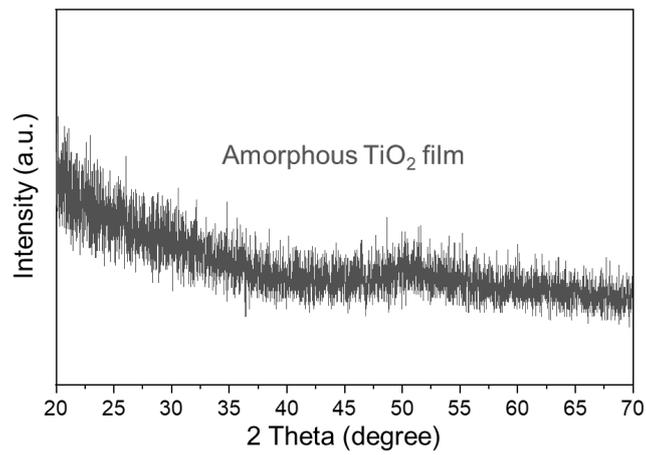


Fig. S9. XRD analysis of the TiO₂ thin film. The 25 nm-thick TiO₂ thin film shows amorphous state.

To investigate the crystalline properties of the bolometric material, we performed X-ray diffraction (XRD) analysis on a 25 nm TiO₂ thin film using a Cu K α source in 2-theta scan mode (Rigaku D/MAX-2500 model at KAIST Analysis Center for Research Advancement, KARA). As depicted in Fig. S9, the diffraction pattern clearly indicated an amorphous state with no sharp peaks, attributed to the insufficient thermal energy required to achieve crystalline phases.

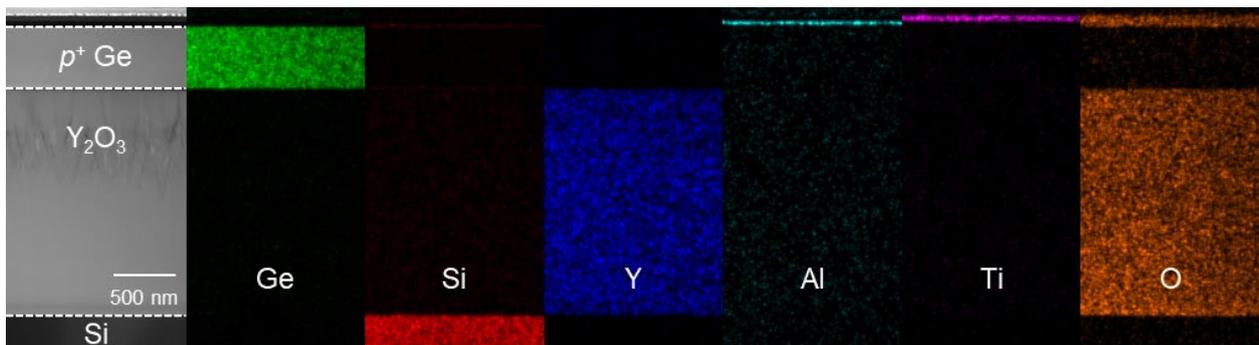


Fig. S10. TEM with EDS analysis. Cross-sectional transmission electron microscopy (TEM) image of the fabricated device with energy-dispersive X-ray spectroscopy (EDS) elemental mapping patterns of Ge, Si, Y, Al, Ti, and O atoms.

Supplementary Note 5. Low-frequency noise analysis

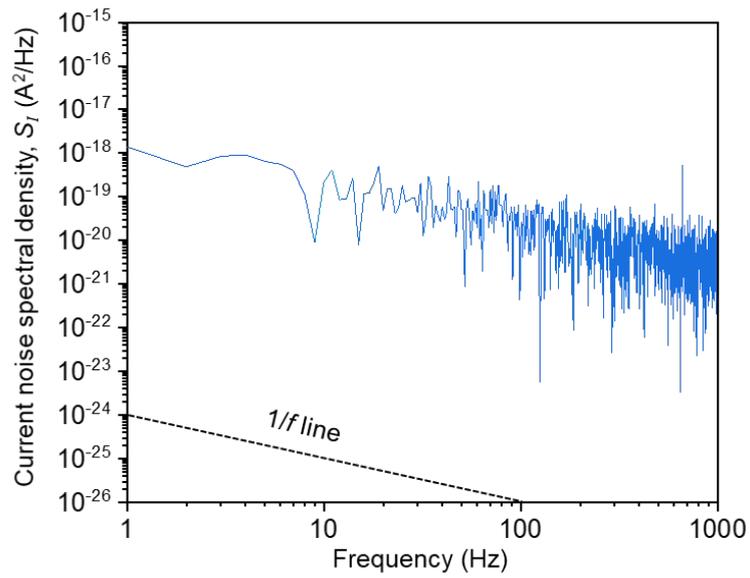


Fig. S11. Low frequency noise (LFN) characteristics. Current noise spectral density, S_I (A²/Hz) of the fabricated device as a function of frequency.

Noise characteristics are critical performance metrics for photonic sensing systems. To estimate the noise-equivalent power (NEP) of our device, we examined the low-frequency noise (LFN) features, i.e., current noise spectral density (A²/Hz), without light coupling (dark state). As shown in Fig. S11, the noise characteristic predominantly follows the 1/ f line (dashed line), indicating that the measured noise primarily arises from flicker noise, also known as 1/ f noise.

Supplementary Note 6. Electrical breakdown characteristics

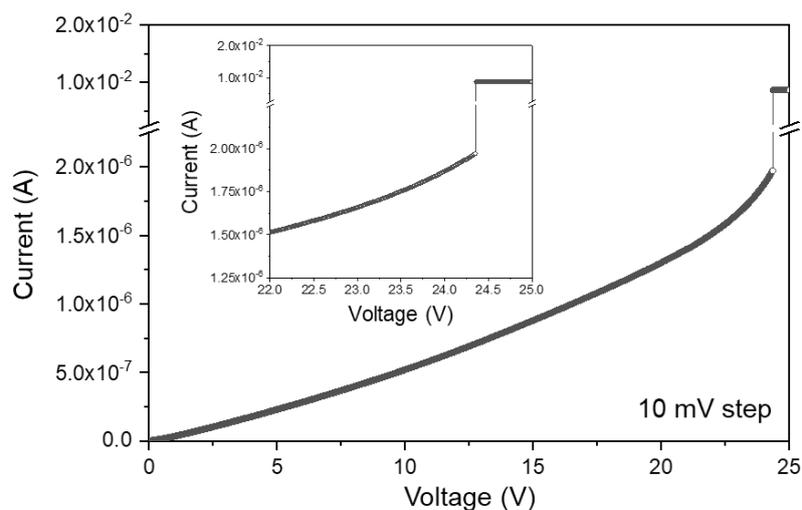


Fig. S12. Electrical breakdown. Current-voltage (I - V) curve of the fabricated device up to 25 V measured at room temperature with a 10-mV interval, indicating the breakdown voltage of ~ 23.8 V.

Figure S12 presents the current-voltage (I - V) characteristics of our device, which were assessed up to a high voltage range of 25 V at room temperature with a voltage step of 10 mV. It was found that the electrical breakdown occurs at ~ 23.8 V, characterized by a rapid change in the slope of the I - V curve. Beyond this voltage range, the device becomes highly conductive, indicating a transition into the breakdown regime where the device exhibits operational failure.

Supplementary Note 7. Propagation loss of waveguides

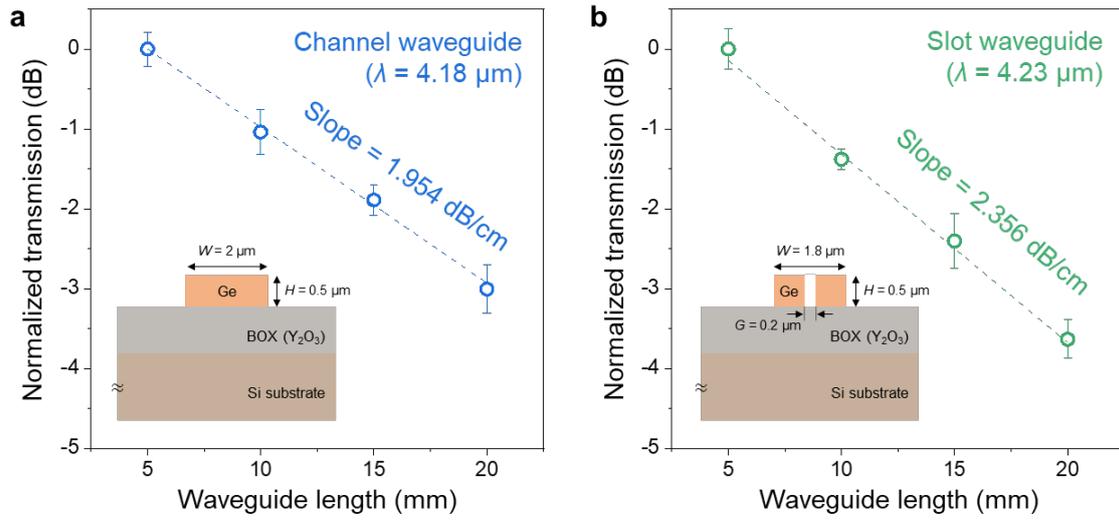


Fig. S13. Propagation losses. **a** Channel waveguide at a wavelength of $4.18 \mu\text{m}$. **b** Slot waveguide at a wavelength of $4.23 \mu\text{m}$.

Figure S13a and S13b show the propagation losses for channel and slot waveguides on the Ge-OI platform, respectively, as depicted in each inset. These losses were characterized using the cut-back method under an N_2 gas purging environment. The results indicate propagation losses of 1.954 dB/cm for the channel waveguide at a wavelength of $4.18 \mu\text{m}$ and 2.356 dB/cm for slot waveguide at $4.23 \mu\text{m}$.

Supplementary Note 8. Simulation of mode converters

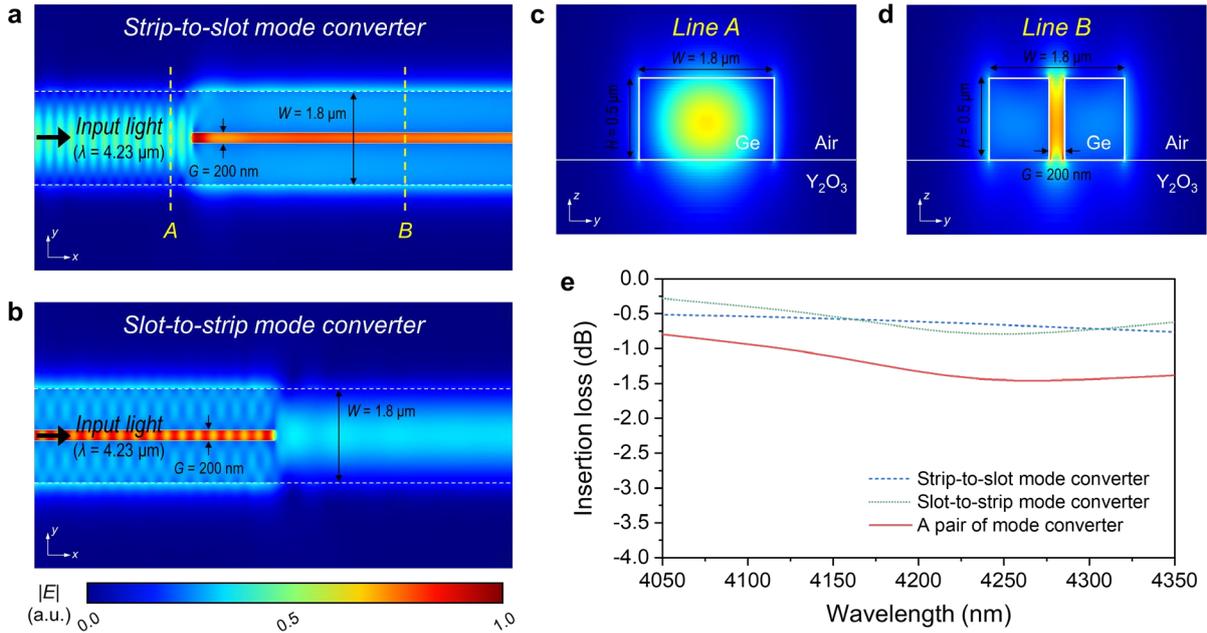


Fig. S14. Mode converters on Ge-OI platform. **a-b** Electric-field distribution for strip-to-slot and slot-to-strip mode converters at a wavelength of 4.23 μm. **c-d** Cross-sectional field distribution along lines *A* and *B* for the channel and slot waveguide regions, respectively. **e** Simulated mode conversion efficiencies for individual converters and a pair of mode converter.

Figures S14a and S14b depict the electric-field distribution of strip-to-slot and slot-to-strip mode converters on the Ge-OI platform at a wavelength of 4.23 μm in fundamental transverse-electric (TE) mode, respectively. The conversion efficiencies between strip and slot modes⁵ were calculated by a 3D-FDTD solver (Ansys Lumerical). Figure S14c and S14d show the cross-sectional field distribution along lines *A* and *B* in the strip and slot regions, respectively, representing well-confined modal fields. The simulated mode conversion efficiencies for the wavelength range from 4050 to 4350 nm are plotted in Fig. S14e. The insertion of a pair of mode converter at 4.23 μm was estimated to be 1.43 dB.

Supplementary Note 9. Performance comparison

Table S1. The overall performance characteristics of the reported MIR waveguide-integrated thermal-type PDs. ChG, chalcogenide glass; BOL, bolometric; PTE, photothermoelectric; TCR, temperature-coefficient of resistance; NEP, noise-equivalent power.

Reference, Year	Ref ⁶ , 2019	Ref ⁷ , 2021	Ref ⁸ , 2022	This work
Operation wavelength	3.72 – 3.88 μm	3.72 – 3.88 μm	5.2 μm	4.03 – 4.36 μm
Photonic platform	Suspended Si (c-Si)	Suspended Si (a-Si)	ChG-on-CaF ₂ (Ge ₂₈ Sb ₁₂ Se ₆₀ -on-CaF ₂)	Ge-OI (Ge-on-insulator)
Operation mechanism	BOL	BOL	PTE	BOL
Absorption material	Au	Au	Graphene	p^+ Ge
Bolometric material	a-Si	a-Si	-	TiO ₂ /Ti/TiO ₂
TCR (-%/K)	0.9	1.9	-	4.262 (@293 K)
Responsivity	2.26×10^{-4} mA/W (@15 V, 3.8 μm)	2.95×10^{-3} mA/W (@10 V, 3.8 μm)	10 mA/W (@0 V)	12.19 mA/W (@3 V, 4.18 μm)
Dark current (nA)	20 (@ 5 V)	12 (@10 V)	Not stated	127.5 (@3 V)
NEP	66 $\mu\text{W}/\text{Hz}^{0.5}$	10.4 $\mu\text{W}/\text{Hz}^{0.5}$	1.1 nW/Hz ^{0.5}	3.4 nW/Hz ^{0.5}
CMOS-compatibility	Low	Low	Low	High

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